



MMDT3904V

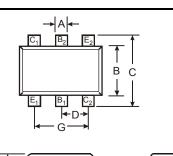
DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

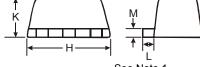
Features

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Terminals: Lead bearing terminal plating available. See Ordering information Page 3
- Marking Information: KAP, See Page 3
- Ordering Information: See Page 3
- Weight: 0.003 grams (approximate)





See Note 1

SOT-563									
Dim	Min	Мах	Тур						
Α	0.15	0.30	0.25						
В	1.10	1.25	1.20						
С	1.55 1.70 1.6								
D	0.50								
G	0.90	1.10	1.00						
Н	1.50	1.70	1.60						
к	0.56	0.60	0.60						
L	0.10	0.30	0.20						
М	M 0.10		0.11						
All I	Dimens	ions in	mm						

Maximum Ratings	$@T_A = 25^{\circ}C$ unless otherwise specified	fied	
Cha	aracteristic	Symbol	Value
Collector Base Voltage		14	60

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	60	V	
Collector-Emitter Voltage	V _{CEO}	40	V	
Emitter-Base Voltage	V _{EBO}	6.0	V	
Collector Current - Continuous	Ι _C	200	mA	
Power Dissipation (Note 2)	Pd	200	mW	
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	625	°C/W	
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C	

1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.65 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

3. No purposefully added lead.

4.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date 5. Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

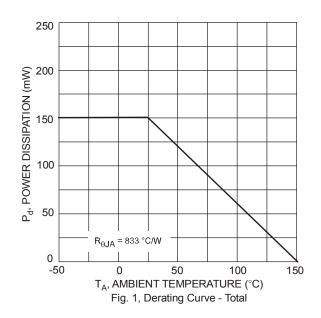
Notes:

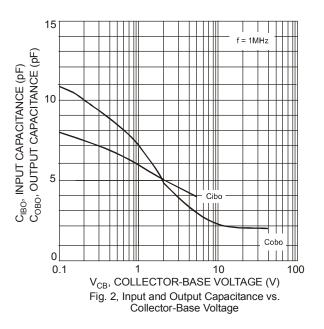


Electrical Characteristics @T_A = 25°C unless otherwise specified

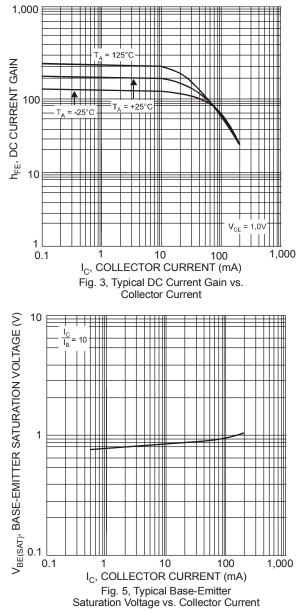
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	·				
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60		V	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40		V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5.0		V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector Cutoff Current	I _{CEX}	_	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
Base Cutoff Current	I _{BL}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 6)	·				
DC Current Gain	h _{FE}	40 70 100 60 30	 300		$\begin{split} I_{C} &= 100 \mu A, V_{CE} = 1.0V \\ I_{C} &= 1.0 m A, V_{CE} = 1.0V \\ I_{C} &= 10 m A, V_{CE} = 1.0V \\ I_{C} &= 50 m A, V_{CE} = 1.0V \\ I_{C} &= 100 m A, V_{CE} = 1.0V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.20 0.30	V	I_{C} = 10mA, I_{B} = 1.0mA I_{C} = 50mA, I_{B} = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	0.85 0.95	V	I_{C} = 10mA, I_{B} = 1.0mA I_{C} = 50mA, I_{B} = 5.0mA
SMALL SIGNAL CHARACTERISTICS		-			-
Output Capacitance	C _{obo}		4.0	pF	V_{CB} = 5.0V, f = 1.0MHz, I _E = 0
nput Capacitance	Cibo	—	8.0	pF	V_{EB} = 0.5V, f = 1.0MHz, I _C = 0
nput Impedance	h _{ie}	1.0	10	kΩ	
/oltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,
Small Signal Current Gain	h _{fe}	100	400	—	f = 1.0kHz
Dutput Admittance	h _{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f _T	300	_	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz
Noise Figure	NF	_	5.0	dB	V _{CE} = 5.0V, I _C = 100μA, R _S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d		35	ns	V _{CC} = 3.0V, I _C = 10mA,
Rise Time	tr		35	ns	$V_{BE(off)}$ = - 0.5V, I _{B1} = 1.0mA
Storage Time	ts		200	ns	V _{CC} = 3.0V, I _C = 10mA,
Fall Time	t _f		50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

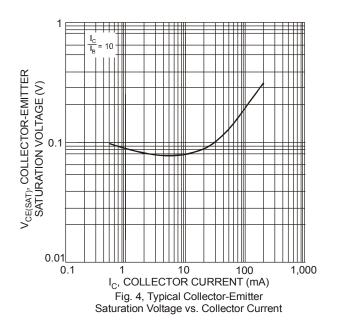
Notes: 6. Short duration pulse test used to minimize self-heating effect.











Ordering Information (Note 7)

Device	Packaging	Shipping			
MMDT3904V-7	SOT-563	3000/Tape & Reel			

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

Date Code Key				<u> П [</u> кар үм	Y Y	M = Date = Year (e	Code Mai ex: R = 200		ode			
Year	2004	20	05	2006	2007	20	08	2009	2010	20	011	2012
Code	R	S	6	Т	U	V		W	Х		Y	Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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